

# MOSFET – N-Channel, SUPERFET® II

## 600 V, 20.2 A, 199 mΩ

### FCPF190N60-F154

#### Description

SUPERFET II MOSFET is onsemi’s brand–new high voltage super–junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on–resistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate and higher avalanche energy. Consequently, SUPERFET II FAST MOSFET series helps minimize various power systems and improve system efficiency.

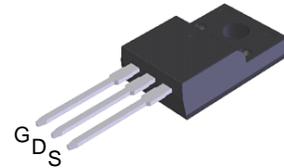
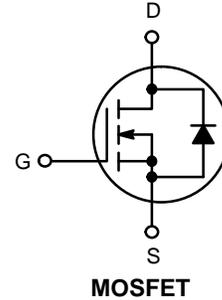
#### Features

- 650 V @  $T_J = 150^\circ\text{C}$
- Typ.  $R_{DS(on)} = 170\text{ m}\Omega$
- Ultra Low Gate Charge (Typ.  $Q_g = 57\text{ nC}$ )
- Low Effective Output Capacitance (Typ.  $C_{oss,eff} = 160\text{ pF}$ )
- 100% Avalanche Tested
- These Devices are Pb–Free and are RoHS Compliant

#### Applications

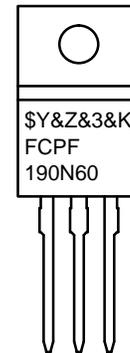
- Computing / Display Power Supplies
- Telecom / Server Power Supplies
- Industrial Power Supplies
- Lighting / Charger / Adapter

$V_{DSS}$	$R_{DS(on)}\text{ MAX}$	$I_D\text{ MAX}$
600 V	199 mΩ @ 10 V	20.2 A



TO–220F Ultra Narrow Lead  
 CASE 221BN

#### MARKING DIAGRAM



- \$Y = onsemi Logo
- &Z = Assembly Plant Code
- &3 = Data Code (Year & Week)
- &K = Lot
- FCPF190N60 = Specific Device Code

#### ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

## FCPF190N60-F154

### ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub> = 25°C, Unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>DSS</sub>	Drain to Source Voltage	600	V
V <sub>GSS</sub>	Gate to Source Voltage	- DC	±20
		- AC (f > 1 Hz)	±30
I <sub>D</sub>	Drain Current	- Continuous (T <sub>C</sub> = 25°C)	20.2*
		- Continuous (T <sub>C</sub> = 100°C)	12.7*
I <sub>DM</sub>	Drain Current	- Pulsed (Note 1)	60.6*
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)	400	mJ
I <sub>AS</sub>	Avalanche Current (Note 2)	4.0	A
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1)	2.1	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	20	V/ns
	MOSFET dv/dt	100	
P <sub>D</sub>	Power Dissipation	(T <sub>C</sub> = 25°C)	39
		- Derate Above 25°C	0.31
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to +150	°C
T <sub>L</sub>	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

\*Drain current limited by maximum junction temperature.

1. Repetitive rating: pulse width limited by maximum junction temperature.
2. I<sub>AS</sub> = 4 A, V<sub>DD</sub> = 50 V, R<sub>G</sub> = 25 Ω, starting T<sub>J</sub> = 25°C.
3. I<sub>SD</sub> ≤ 10 A, di/dt ≤ 200 A/μs, V<sub>DD</sub> ≤ BV<sub>DSS</sub>, starting T<sub>J</sub> = 25°C.

### THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
R <sub>θJC</sub>	Thermal Resistance, Junction to Case, Max.	3.2	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient, Max.	62.5	°C/W

### PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Shipping
FCPF190N60-F154	FCPF190N60	TO-220F (Pb-Free)	50 Units / Tube

# FCPF190N60-F154

## ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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### OFF CHARACTERISTICS

BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 10 mA, T <sub>J</sub> = 25°C	600	–	–	V
		V <sub>GS</sub> = 0 V, I <sub>D</sub> = 10 mA, T <sub>J</sub> = 150°C	650	–	–	V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 10 mA, Referenced to 25°C	–	0.67	–	V/°C
BV <sub>DS</sub>	Drain–Source Avalanche Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 20 A	–	700	–	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 480 V, V <sub>GS</sub> = 0 V	–	–	10	μA
		V <sub>DS</sub> = 480 V, T <sub>C</sub> = 125°C	–	–	10	
I <sub>GSS</sub>	Gate to Body Leakage Current	V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0 V	–	–	±100	nA

### ON CHARACTERISTICS

V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 250 μA	2.5	–	3.5	V
R <sub>DS(on)</sub>	Static Drain to Source On Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A	–	0.17	0.199	Ω
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 20 V, I <sub>D</sub> = 10 A	–	21	–	S

### DYNAMIC CHARACTERISTICS

C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz	–	2220	2950	pF
C <sub>oss</sub>	Output Capacitance		–	1630	2165	pF
C <sub>riss</sub>	Reverse Transfer Capacitance		–	85	128	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> = 380 V, V <sub>GS</sub> = 0 V, f = 1 MHz	–	42	–	pF
C <sub>oss (eff.)</sub>	Effective Output Capacitance	V <sub>DS</sub> = 0 V to 480 V, V <sub>GS</sub> = 0 V	–	160	–	pF
Q <sub>g(tot)</sub>	Total Gate Charge at 10 V	V <sub>DS</sub> = 380 V, I <sub>D</sub> = 10 A, V <sub>GS</sub> = 10 V (Note 4)	–	57	74	nC
Q <sub>gs</sub>	Gate to Source Gate Charge		–	9	–	nC
Q <sub>gd</sub>	Gate to Drain "Miller" Charge		–	21	–	nC
ESR	Equivalent Series Resistance	f = 1 MHz	–	1	–	Ω

### SWITCHING CHARACTERISTICS

t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 380 V, I <sub>D</sub> = 10 A, V <sub>GS</sub> = 10 V, R <sub>g</sub> = 4.7 Ω (Note 4)	–	20	50	ns
t <sub>r</sub>	Turn-On Rise Time		–	10	30	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		–	64	138	ns
t <sub>f</sub>	Turn-Off Fall Time		–	5	20	ns

### SOURCE-DRAIN DIODE CHARACTERISTICS

I <sub>S</sub>	Maximum Continuous Source to Drain Diode Forward Current	–	–	20.2	A	
I <sub>SM</sub>	Maximum Pulsed Source to Drain Diode Forward Current	–	–	60.6	A	
V <sub>SD</sub>	Source to Drain Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 10 A	–	–	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>DD</sub> = 400 V, I <sub>SD</sub> = 10 A, dI <sub>F</sub> /dt = 100 A/μs	–	280	–	ns
Q <sub>rr</sub>	Reverse Recovery Charge		–	3.8	–	μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Essentially independent of operating temperature typical characteristics.

TYPICAL PERFORMANCE CHARACTERISTICS

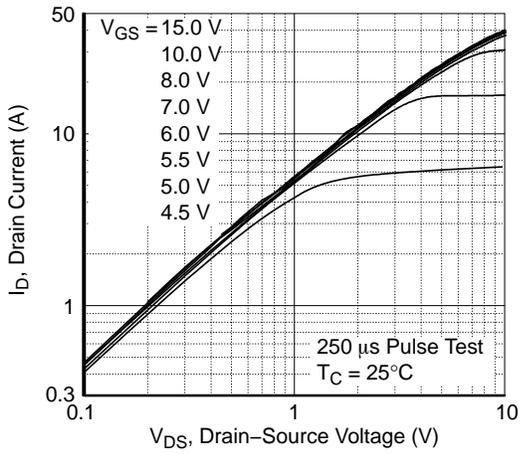


Figure 1. On-Region Characteristics

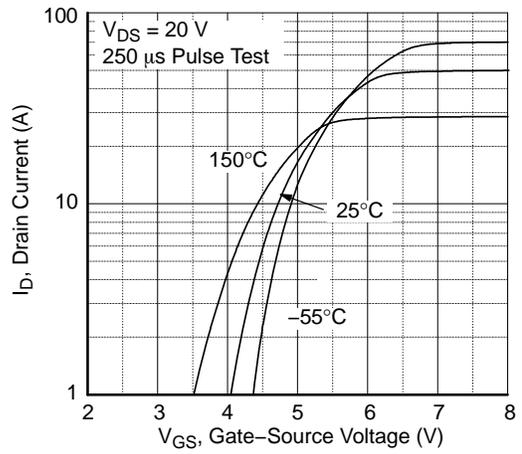


Figure 2. Transfer Characteristics

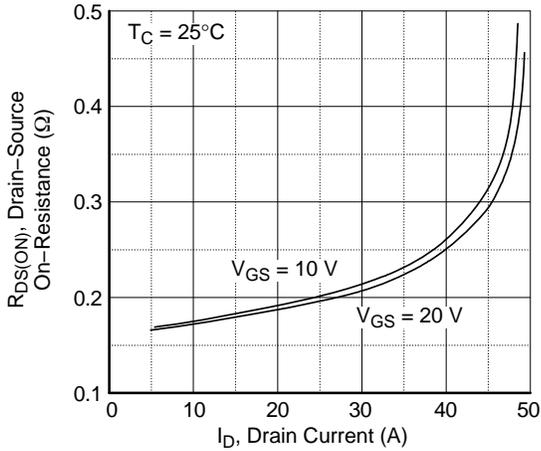


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

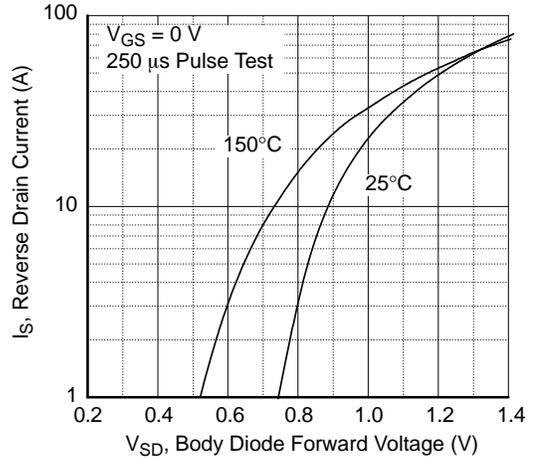


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

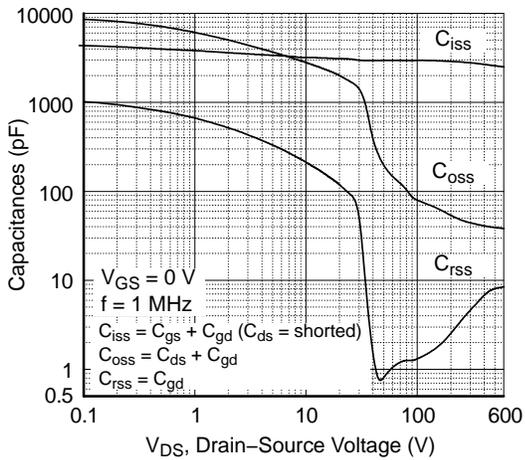


Figure 5. Capacitance Characteristics

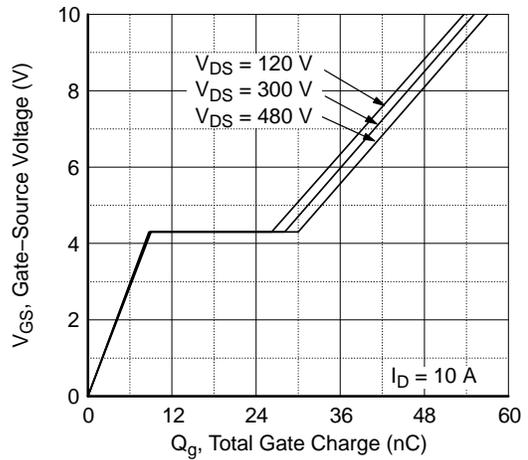


Figure 6. Gate Charge Characteristics

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

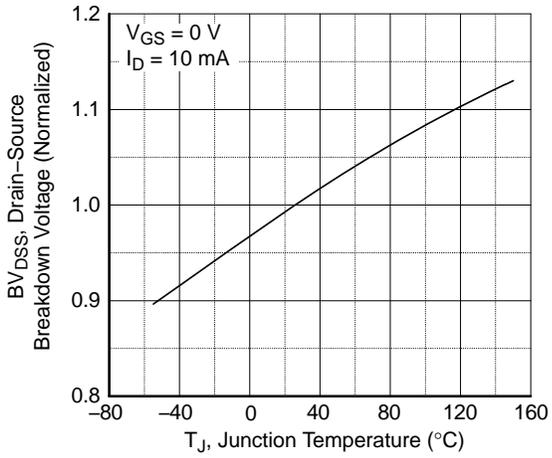


Figure 7. Breakdown Voltage Variation vs. Temperature

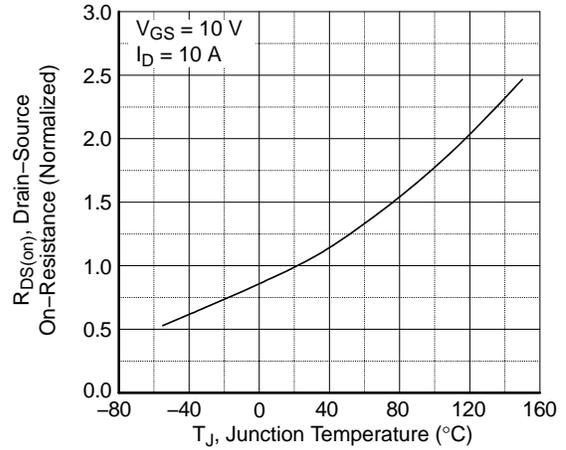


Figure 8. On-Resistance Variation vs. Temperature

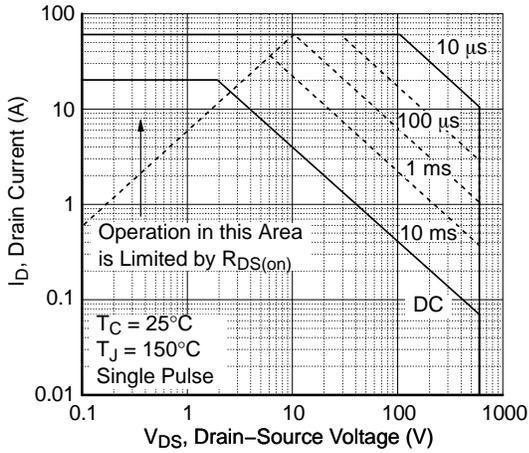


Figure 9. Maximum Safe Operating Area

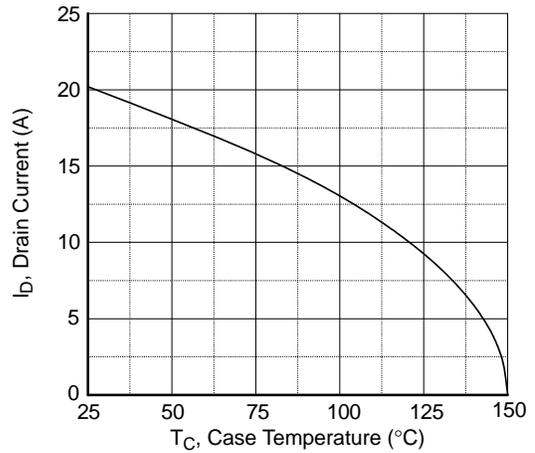


Figure 10. Maximum Drain Current vs. Case Temperature

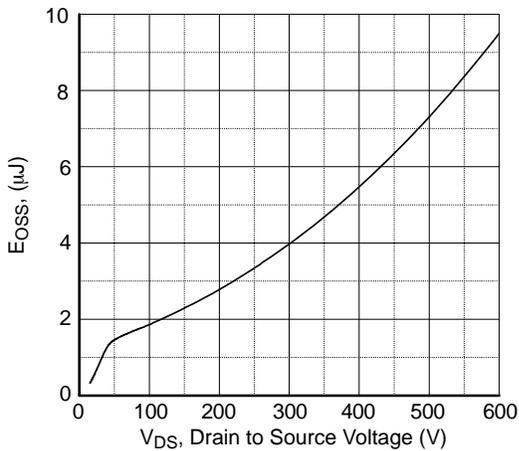


Figure 11.  $E_{OSS}$  vs. Drain-to-Source Voltage

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## TYPICAL PERFORMANCE CHARACTERISTICS (continued)

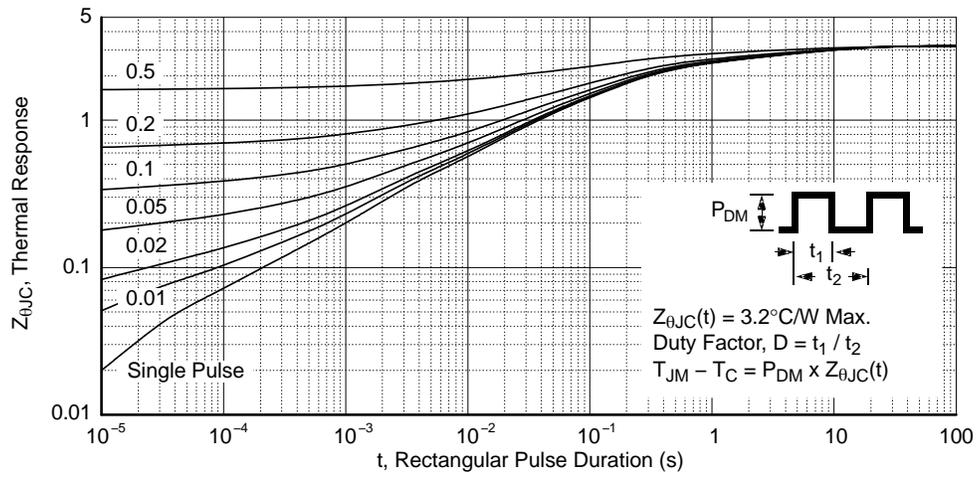


Figure 12. Transient Thermal Response Curve

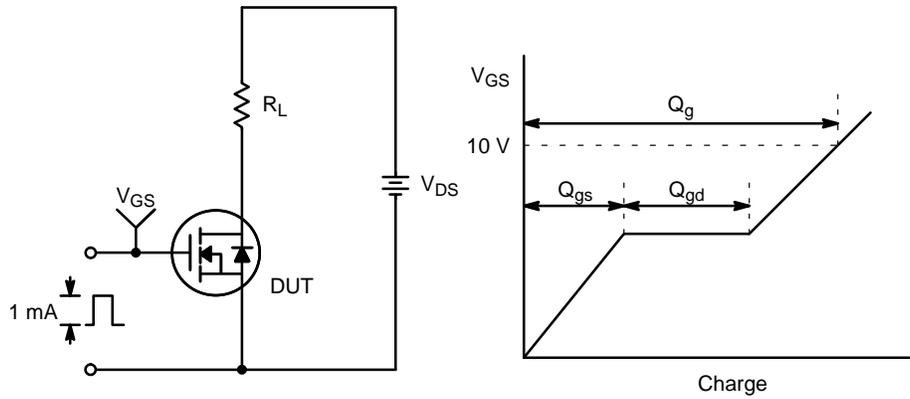


Figure 13. Gate Charge Test Circuit & Waveform

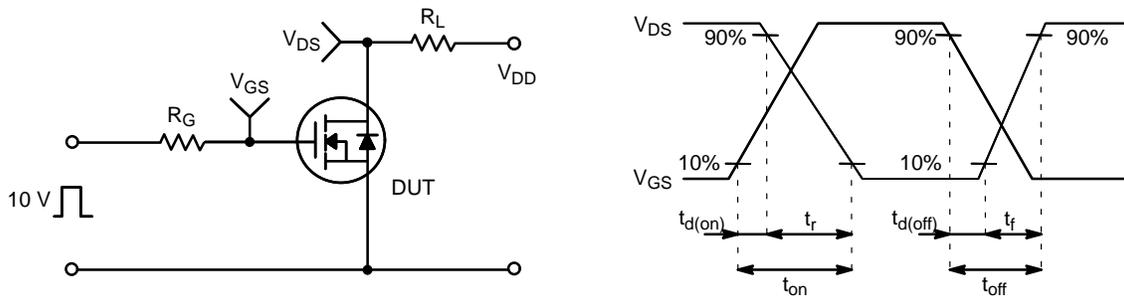


Figure 14. Resistive Switching Test Circuit & Waveforms

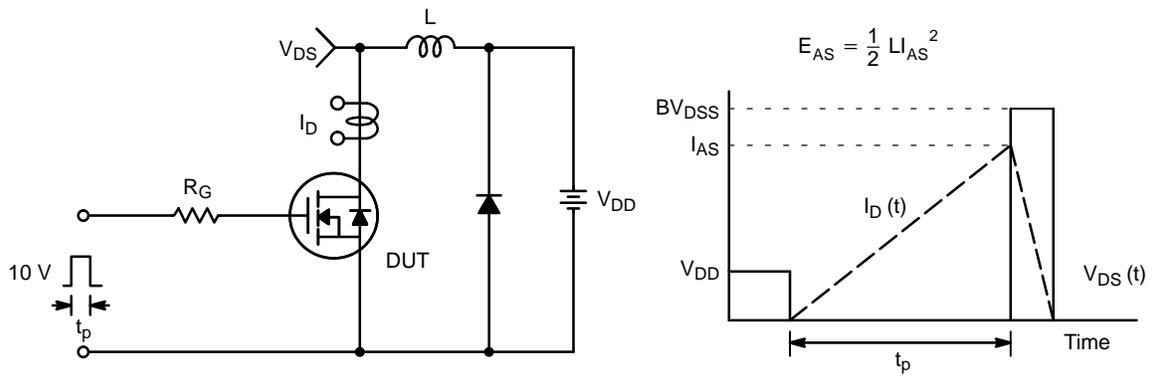
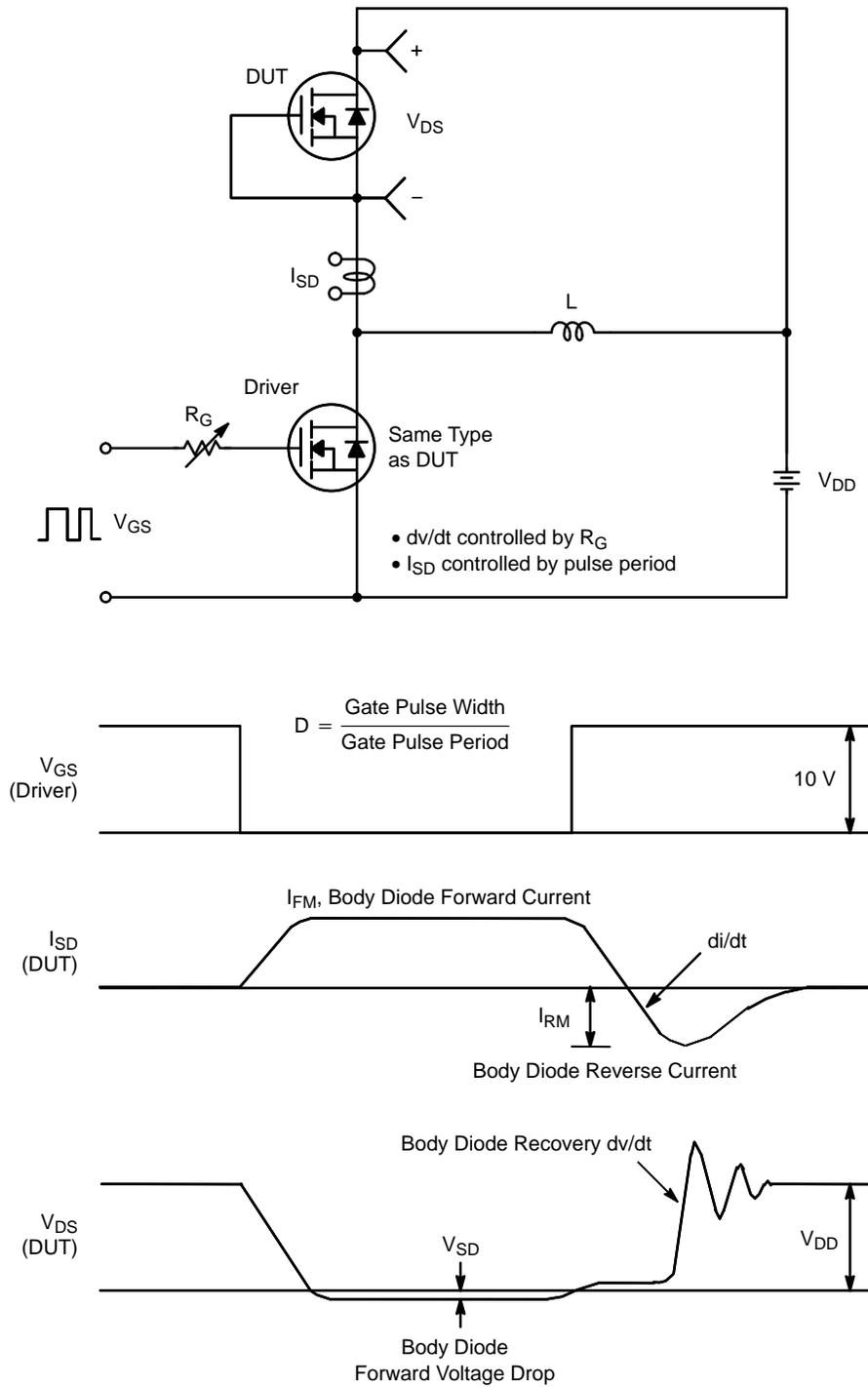


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

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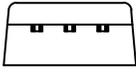


**Figure 16. Peak Recovery  $dv/dt$  Test Circuit & Waveforms**

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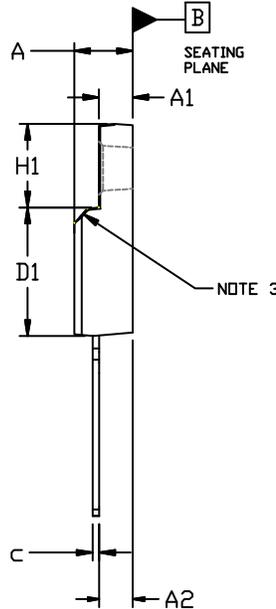
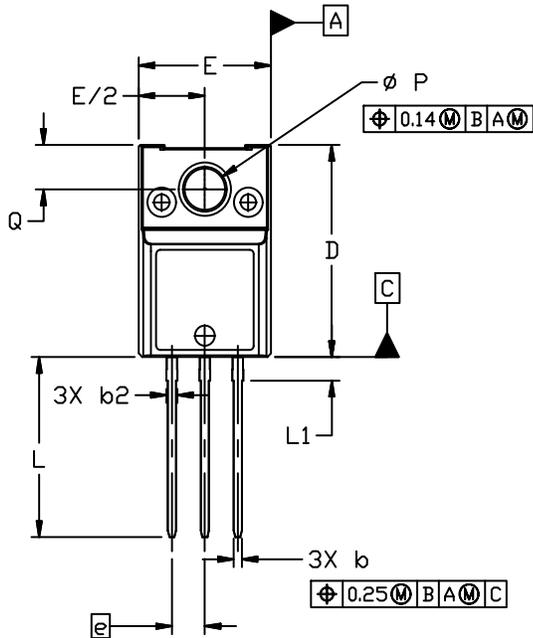
## PACKAGE DIMENSIONS

### TO-220 FULLPACK, 3-LEAD CASE 221BN ISSUE O



#### NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. CONTOUR UNCONTROLLED IN THIS AREA.
4. DIMENSIONS EXCLUDE BURRS, MOLD FLASH, AND TIE BAR PROTRUSIONS.



DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	4.60	4.70	4.80
A1	2.50	2.60	2.70
A2	2.47	2.57	2.67
b	0.56	0.63	0.69
b2	---	---	0.90
c	0.46	0.53	0.59
D	15.80	16.00	16.20
D1	9.58	9.68	9.78
E	10.00	10.20	10.40
e	2.54 BSC		
H1	6.32 REF		
L	13.45	13.60	13.75
L1	1.70	1.80	1.90
P	3.00	3.10	3.20
Q	3.25	3.35	3.45

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